

L-BAND PA DRIVER AMPLIFIER

DESCRIPTION

NEC

The μ PG2126TB is a GaAs MMIC for PA driver amplifier which were developed for dual band mobile phone and another L-band application. The device can operate with 3.6 V TYP., having the high gain and low distortion.

FEATURES

	 Supply voltage 	: VDD1, 2, 3 = 3.1 to 4.4 V (3.6 V TYP.)
\star	 Low operation current 	: IDD1 = 16 mA TYP. @ VDD1 = 3.6 V, f = 925 MHz, Pout = +8 dBm
*		: IDD2 = 28 mA TYP. @ VDD2, 3 = 3.6 V, f = 1 441 MHz, Pout = +8 dBm
\star	High power gain	: GP1 = 16 dB TYP. @ VDD1 = 3.6 V, f = 925 MHz, Pin = -10 dBm
*		: GP2 = 26 dB TYP. @ Vdd2, 3 = 3.6 V, f = 1 441 MHz, Pin = -22 dBm
	Low distortion	: Padj1 = -60 dBc TYP. @ VDD1, 2, 3 = 3.6 V, f = 925 MHz, 1 441 MHz, Pout = +8 dBm,
		$\Delta f = \pm 50 \text{ kHz}$, 21 kHz Bandwidth.

• High-density surface mounting : 6-pin super minimold package ($2.0 \times 1.25 \times 0.9$ mm)

APPLICATION

• Digital Cellular: dual band mobile phone etc.

ORDERING INFORMATION

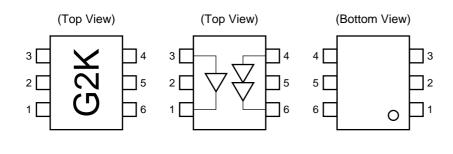
Part Number	Package	Marking	Supplying Form
μPG2126TB-E3	6-pin super minimold	G2K	Embossed tape 8 mm widePin 1, 2, 3 face the perforation side of the tapeQty 3 kpcs/reel

Remark To order evaluation samples, contact your nearby sales office. Part number for sample order: μ PG2126TB

Caution Electro-static sensitive devices

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

PIN CONNECTIONS, MARKING AND INTERNAL BLOCK DIAGRAM



Pin No.	Pin Name	
1	VDD1/OUTPUT1	
2	GND	
3	INPUT1	
4	INPUT2	
5	Vdd2	
6	VDD3/OUTPUT2	

ABSOLUTE MAXIMUM RATINGS (Unless otherwise specified, TA = +25°C)

Parameter	Symbol	Ratings	Unit
Supply Voltage1, 2, 3	Vdd1, 2, 3	6.0	V
Input Power 1 (INPUT1)	Pin1	+4	dBm
Input Power 2 (INPUT2)	Pin2	-4	dBm
Power Dissipation	PD	140 ^{Note}	mW
Operating Ambient Temperature	TA	-30 to +90	°C
Storage Temperature	Tstg	-35 to +150	°C

*

Note Mounted on double copper-clad $50 \times 50 \times 1.6$ mm epoxy glass PWB, T_A = +85°C

RECOMMENDED OPERATING RENGE (TA = +25°C)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage1, 2, 3	Vdd1, 2, 3	3.1	3.6	4.4	V
Input Power 1 (INPUT1)	Pin1	-	-	-10	dBm
Input Power 2 (INPUT2)	Pin2	-	-	-20	dBm
Operating Frequency 1	fopt1	893	-	960	MHz
Operating Frequency 2	fopt2	1 429	-	1 453	MHz

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ELECTRICAL CHARACTERISTICS -INPUT1-OUTPUT1-

(Unless otherwise specified, T_A = +25°C, V_{DD1} = 3.6 V, π /4DQPSK modulated signal input, External input and output matching)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Operating Frequency 1	fopt1		893	925	960	MHz
Power Gain 1	G _{P1}	$P_{in} = -10 \text{ dBm}$	14	16	18	dB
Circuit Current 1	DD1	P _{out} = +8 dBm	-	16	20	mA
Adjacent Channel Power Leakage 1	Padj1	$P_{out} = +8 \text{ dBm},$ $\Delta f = \pm 50 \text{ kHz}, 21 \text{ kHz Bandwidth}$	-	-60	-55	dBc
Adjacent Channel Power Leakage 2	Padj2	$P_{out} = +8 \text{ dBm},$ $\Delta f = \pm 100 \text{ kHz}, 21 \text{ kHz Bandwidth}$	-	-70	-65	dBc

ELECTRICAL CHARACTERISTICS -INPUT2-OUTPUT2-

(Unless otherwise specified, $T_A = +25^{\circ}C$, $V_{DD2} = V_{DD3} = 3.6 \text{ V}$, $\pi/4DQPSK$ modulated signal input, External input and output matching)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Operating Frequency 2	fopt2		1 429	1 441	1 453	MHz
Power Gain 2	Gp2	$P_{in} = -22 \text{ dBm}$	24	26	28	dB
Circuit Current 2	IDD2	P _{out} = +8 dBm	-	28	32	mA
Adjacent Channel Power Leakage 3	Padj3	$P_{out} = +8 \text{ dBm},$ $\Delta f = \pm 50 \text{ kHz}, 21 \text{ kHz Bandwidth}$	-	-60	-55	dBc
Adjacent Channel Power Leakage 4	Padj4	$P_{out} = +8 \text{ dBm},$ $\Delta f = \pm 100 \text{ kHz}, 21 \text{ kHz Bandwidth}$	-	-70	-65	dBc

Data Sheet PG10019EJ02V0DS

VDD1 Ο 100 pF 8.2 nH 8.2 nH 2 pF 1.5 pF OUT1 O ┨┠ O IN1 1 2 3 G2 < 4 6 5 3 pF 8.2 nH OUT2 O ╢ M O 1N2 E 2.2 nH 12 nH 1.5 pF 7/7 100 pF 100 pF Ο Ο Vdd3 Vdd2

EVALUATION CIRCUIT (VDD1, 2, 3 = 3.6 V, f = 925 MHz (INPUT1-OUTPUT1), f = 1 441 MHz (INPUT2-OUTPUT2))

The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

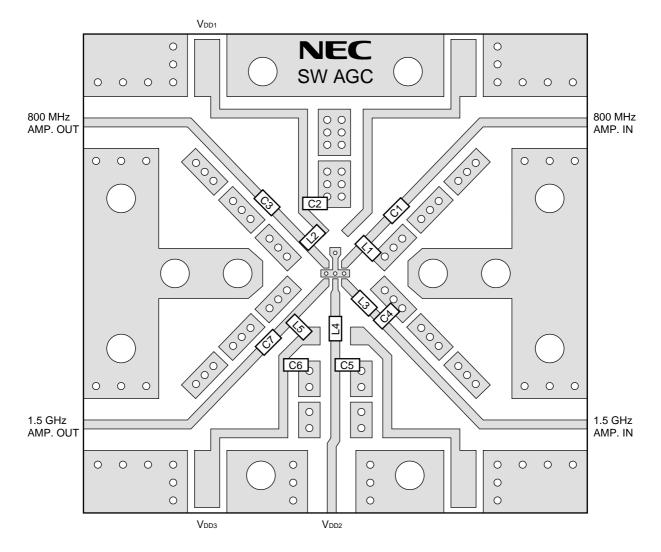


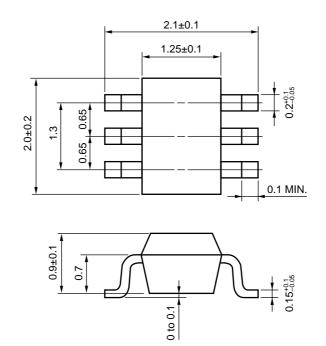
ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD

COMPONENT LIST

Symbol	Rating	Part Number	Munufacturer
L1, L2, L3	8.2 nH	TFL0816-8N2	Susumu
L4	2.2 nH	TFL0816-2N2	Susumu
L5	12 nH	TFL0816-12N	Susumu
C1, C4	1.5 pF	GRM39CK1R5C50	muRata
C2, C5, C6	100 pF	GRM39CH101J50	muRata
C3	2 pF	GRM39CK020C50	muRata
C7	3 pF	GRM39CJ030C50	muRata

PACKAGE DIMENSIONS

6-PIN SUPER MINIMOLD (UNIT: mm)



RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) Time at temperature of 200°C or higher Preheating time at 120 to 150°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 215°C or below : 25 to 40 seconds : 30 to 60 seconds : 3 times : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).

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(Note)

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- (2) "NEC semiconductor products" means any semiconductor product developed or manufactured by or for NEC (as defined above).

M8E 00.4-0110

SAFETY INFORMATION ON THIS PRODUCT

Caution GaAs Products	The product contains gallium arsenide, GaAs. GaAs vapor and powder are hazardous to human health if inhaled or ingested.					
	Do not destroy or burn the product.					
	Do not cut or cleave off any part of the product.					
	Do not crush or chemically dissolve the product.					
	Do not put the product in the mouth.					
	Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.					

▶Business issue

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